



SLS SEMICONDUCTOR (SHENZHEN) CO.,LTD.

SOD-323 封装二极管/SOD-323 Plastic-Encapsulate Diodes

BAV19WS/BAV20WS/BAV21WS (FAST SWITCHING DIODES)

特点/Features :

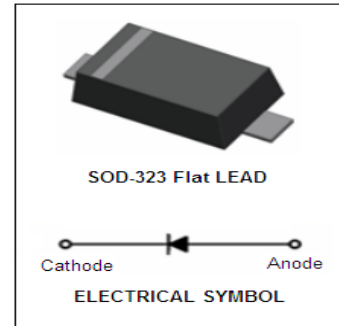
- 速度快 ;
- 尺寸小 , 适合各种有尺寸要求场合 ;

印章/ Marking:

BAV19WS: **A8**

BAV20WS: **T2**

BAV21WS: **T3**



极限参数/Absolute maximum ratings(Ta=25°C)

参数	符号	BAV19WS	BAV20WS	BAV21WS	单位
Non-Repetitive Peak Reverse Voltage	V_{RM}	120	200	250	V
Peak Repetitive Peak Reverse Voltage	V_{RRM}	100	150	250	V
Working Peak Reverse Voltage	V_{RWM}	100	150	250	V
DC Blocking Voltage	V_R	100	150	250	V
RMS Reverse Voltage	$V_{R(RMS)}$	71	106	141	V
Forward Continuous Current	I_{FM}	400			mA
Average Rectified Output Current	I_O	200			mA
Peak Forward Surge Current	I_{FSM}	2.5 (@=1.0mS)			A
		0.5 (@=1.0S)			
Repetitive Peak Forward Current	I_{FRM}	625			mA
Power Dissipation	P_D	0.25			W
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	500			°C/W
Storage Temperature	T_{stg}	-55~150			°C

电性能参数/Electrical characteristics (Ta=25°C)

参数/Parameter	符号	测试条件	最大值	单位
正向电压/Forward Voltage	V_{F1}	$I_F=100mA$	1.0	V
	V_{F2}	$I_F=200mA$	1.25	V
反向漏电流/Reverse Current BAV19WS BAV20WS BAV21WS	I_R	$V_R=100V$	0.1	μA
		$V_R=150V$	0.1	μA
		$V_R=200V$	0.1	μA
端电容/Capacitance Between Terminals	C_T	$V_R=0, f=1MHz$	5	pF
反向恢复时间/Reverse Recovery Time	t_{rr}	$I_F=I_R=30mA,$ $I_{rr}=0.1 \times I_R, R_L=100 \Omega$	50	nS